MULTI-CHIP TRANSISTOR (PNP)

Plastic-Encapsulate Transistor

FEATURES

Power dissipation

P_{CM} : 300mW (Tamb=25°C)

Collector current

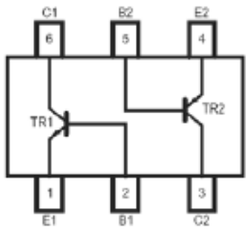
I_{CM} : -200mA

Collector-base Voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C



MARKING: 3C

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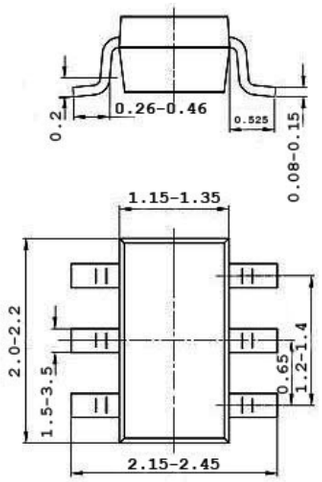

UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=-10μA, I_E=0	-50			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-45			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-10μA, I_C=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V, I_E=0			-15	nA
DC Current Gain	h_{FE}	V_{CE}=-5V, I_C=-2mA	125		630	
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$ $V_{CE(sat)(2)}$	I_C=-10mA, I_B=-0.5mA I_C=-100mA, I_B=-5mA			-0.3 -0.65	V V
Base-Emitter Voltage	$V_{BE(1)}$ $V_{BE(2)}$	V_{CE}=-5V, I_C=-2mA V_{CE}=-5V, I_C=-10mA	-0.6		-0.75 -0.82	V V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=100MHz		200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		3.5		pF
Noise Figure	NF	V_{CE}=-5V, I_C=-0.2mA, f=1KHz, Rs=2KΩ, BW=200Hz		2.5		dB